



#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>A</sub> = +25°C
-12V	$50m\Omega$ @ $V_{GS} = -4.5V$	-4.8A
	65mΩ @ V <sub>GS</sub> = -2.5V	-4.2A

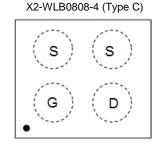
## **Description**

This new generation MOSFET has been designed to minimize the onstate resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications. It is a high performance MOSFET in ultra-small 0.8mm x0.8mm package.

## **Applications**

- Portable Applications
- Load Switch
- Power Management Functions

# ESD PROTECTED



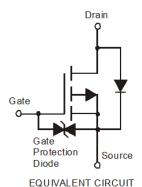
Top View

## **Features and Benefits**

- Ultra Small 0.8mm x 0.8mm Package
- Built-in G-S Protection Diode Against ESD
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

## **Mechanical Data**

- Case: X2-WLB0808-4
- Terminal Connections: See Diagram Below
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish —SnAgCu. Solderable per MIL-STD-202 Method 208
- Weight: 0.0011 grams (Approximate)



## Ordering Information (Note 4)

Ì	Part Number	Case	Packaging
	DMP1045UCB4-7	X2-WLB0808-4 (Type C)	3000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

# Marking Information



9M = Product Type Marking Code YM = Date Code Marking Y or  $\overline{Y}$  = Year (ex: G = 2019) M or  $\overline{M}$  = Month (ex: 9 = September)

#### Date Code Key

Year	2019	2020	2021	2022	2023	2024	2025
Code	G	Н		J	K	L	M

Ī	Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Code	1	2	3	4	5	6	7	8	9	0	N	D



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	-12	V		
Gate-Source Voltage			$V_{GSS}$	±8	V
Continuous Drain Current (Note 7) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-2.6 -2.1	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = -4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	-4.8 -3.8	А

## **Thermal Characteristics**

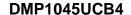
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P <sub>D</sub>	0.53	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 7)	R <sub>θJA</sub>	238	°C/W
Power Dissipation (Note 5)	P <sub>D</sub>	1.75	W
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)	$R_{\theta JA}$	71	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# **Electrical Characteristics** (@T<sub>A</sub> = ±25°C, unless otherwise specified.)

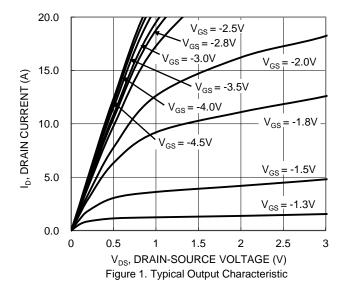
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-12	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	_	_	-1	μA	$V_{DS} = -9.6V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μA	$V_{GS} = \pm 8V$ , $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	-0.67	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$	
		_	42	50		$V_{GS} = -4.5V, I_D = -2A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	51	65	mΩ	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -2A	
		_	67	100		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1A	
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	$V_{GS} = 0V, I_{S} = -1.5A$	
DYNAMIC CHARACTERISTICS (Note 9)	•				,		
Input Capacitance	C <sub>iss</sub>	_	535	_			
Output Capacitance	Coss	_	136	_	pF	$V_{DS} = -6V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	70	_		I = 1.0WI IZ	
Total Gate Charge	Qg	_	6.1	_		4.514.14	
Gate-Source Charge	Qgs	_	0.4	_	nC	$V_{GS} = -4.5V, V_{DD} = -6V,$	
Gate-Drain Charge	Q <sub>gd</sub>	_	2.0	_		$I_D = -2A$	
Turn-On Delay Time	t <sub>D(ON)</sub>	_	28.8	_			
Turn-On Rise Time	t <sub>R</sub>	_	11.3	_		$V_{DD} = -6V, I_D = -2A$	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	115.0	_	ns	$V_{GEN} = -4.5V$ , $R_g = 3\Omega$	
Turn-Off Fall Time	t <sub>F</sub>	_	44.6	_			

Notes:

- 5. Device mounted on FR-4 material with 1-inch<sup>2</sup> (6.45-cm<sup>2</sup>), 2-oz. (0.071-mm thick) Cu.
- 6. Repetitive rating, pulse width limited by junction temperature.
- 7. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided. 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to production testing.







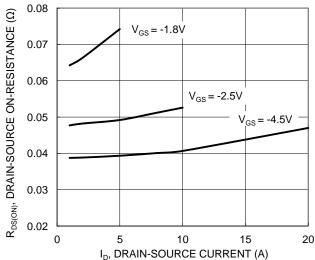


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

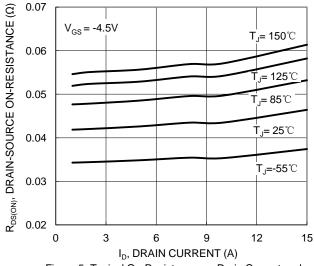


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

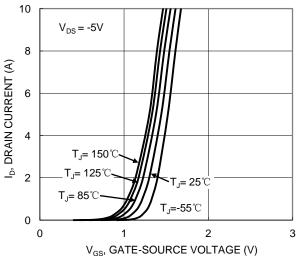
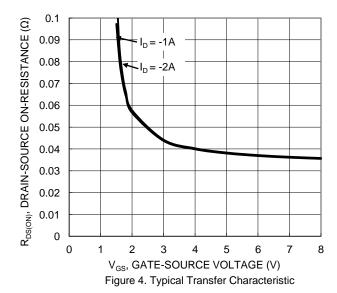


Figure 2. Typical Transfer Characteristic



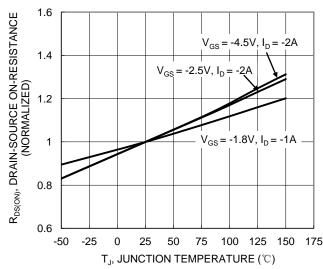


Figure 6. On-Resistance Variation with Temperature





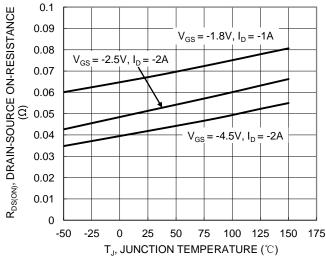


Figure 7. On-Resistance Variation with Temperature

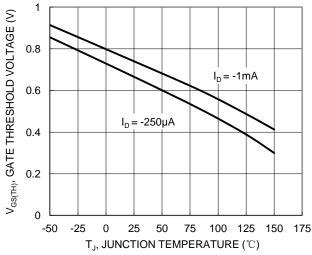


Figure 8. Gate Threshold Variation vs. Junction Temperature

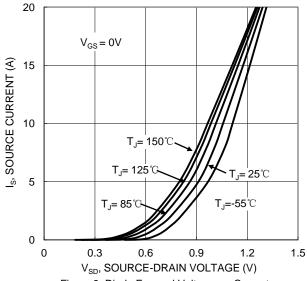
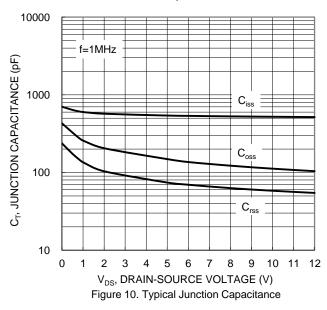
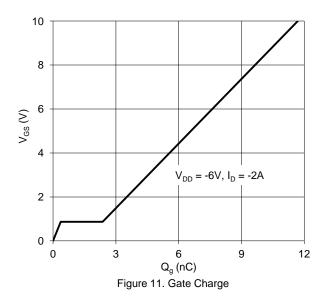
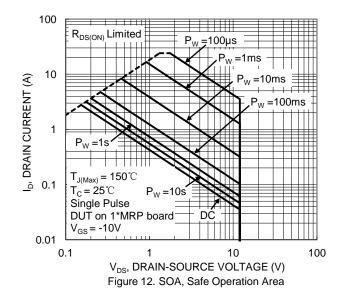


Figure 9. Diode Forward Voltage vs. Current









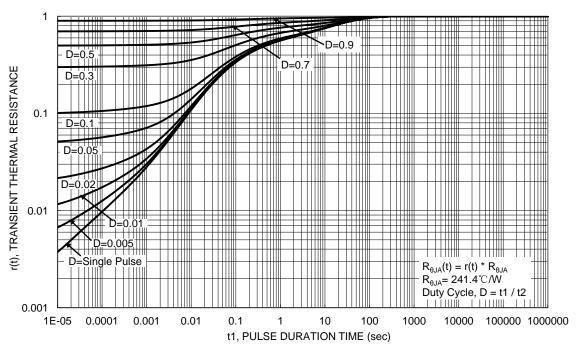


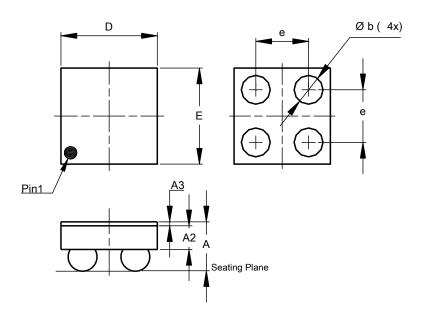
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### X2-WLB0808-4 (Type C)

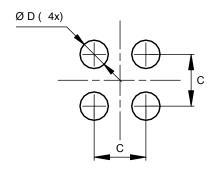


X2-WLB0808-4								
	(1)	ype C)						
Dim	Min	Max	Тур					
Α		0.4000	0.3750					
A2			0.1800					
A3	0.0200	0.0300	0.0250					
b	0.1971	0.2409	0.2190					
D	0.7400	0.8000	0.7700					
Е	0.7400	0.8000	0.7700					
е			0.4000					
Α	All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

## X2-WLB0808-4 (Type C)



Dimensions	Value (in mm)
С	0.400
D	0.219



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